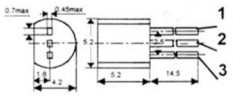
ML 406

Silicon controlled rectifier (SCR)
in TO-92 package



Pinouts:
1- Anode, 2- Gate, 3- Cathode

Maximum ratings

Symbol	Parameter, units		Limits
V_{drm}	Peak repetitive forward voltage, V,	R_{gk} =1kΩ	400
V_{rrm}	Repetitive peak reverse voltage, V		6
$I_{t(rms)}$	On-state curent, A	All Conduction Angles	0.8
$I_t(A_v)$	Average on-state curent, A	Half Cycle, θ=180°,	0.5
$I_{t(sm)}$	Nonrepertition on-state curent, A	Half Cycle, 50Hz	7.0
V_{grm}	Peak reverse gate voltage, V	I_{gr}=0.01mA	6.0

Electrical characteristics (T_A = 25°C)

Symbol	Parameter, units test conditions	Limits	
		min	max
I_{drm}	Off state leakage current, μA, @V_{drm}, R_{gk}=1kΩ		1
V_t	On state voltage, V, I_t=1.2A		1.93
I_{gt}	Gate trigger current, mA, V_g=6V		0.12
V_{gt}	Gate trigger voltage, V, V_g=6V		0.8
I_h	Holding current, mA, R_{gk}=1kΩ		5
dV/dt	Crit. rate of voltage rise, V/μs, V_d=0,67V_{drm}, R_{gk}=1kΩ	25	
dI/dt	Crit. rate of current rise, A/μs, I_g=10mA, dI_g/dt=0,1A/μs	30	
t_{gd}	Gate control delay time, ns, I_g=10mA, dI_g/dt=0,1A/μs		200